



## JST41TE Series 41A TRIACs

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JST41TE series triacs, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

Symbol	Value	Unit
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( $T_j=25$  unless otherwise specified)

### 3 Quadrants

Symbol	Test Condition	Quadrant		Value	Unit
$I_{GT}$	$V_D=12V R_L=33$	- -	MAX	50	mA
$V_{GT}$		- -	MAX	1.3	V
$V_{GD}$	$V_D=V_{DRM} T_j=125$ $R_{\alpha} \quad \alpha$				



Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=60A$ $t_P=380\mu s$	$T_j=25$	1.55	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.85	V
$R_d$	Dynamic resistance	$T_j=125$	9	m
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	10	$\mu A$
$I_{RRM}$		$T_j=125$	5	mA

Symbol	Parameter	Value	Unit
$R_{\dot{A}}$	$x \cdot Q$		



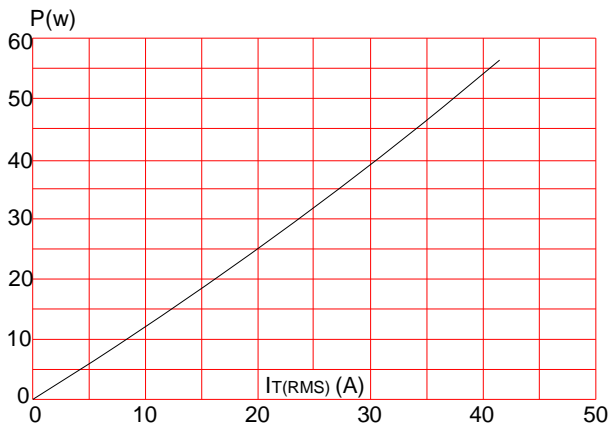
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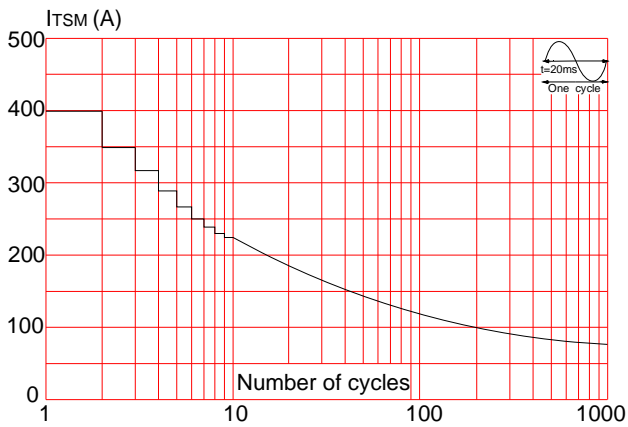
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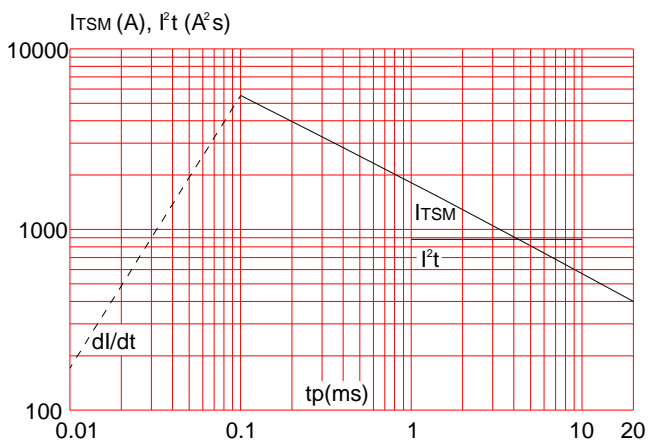
**FIG.1** Maximum power dissipation versus RMS on-state current



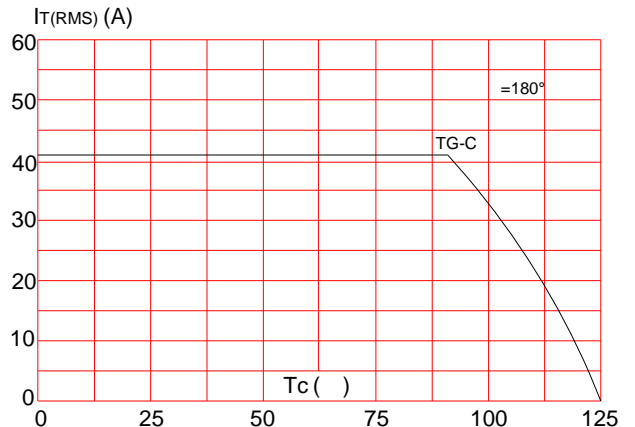
**FIG.3:** Surge peak on-state current versus number of cycles



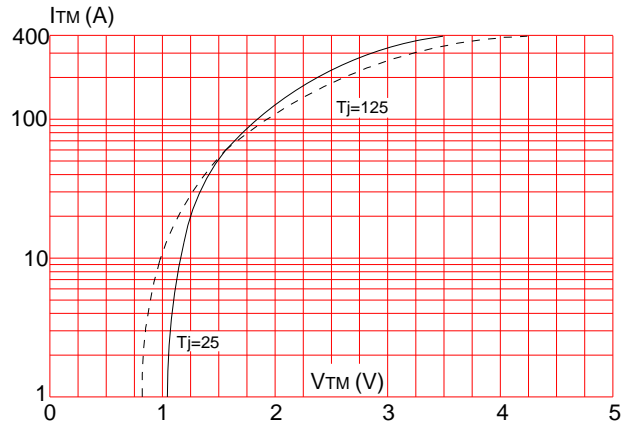
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t (dI/dt < 50\text{A}/\mu\text{s})$



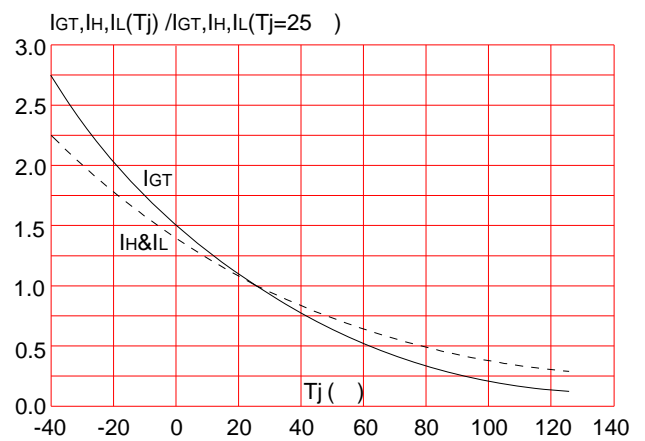
**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature





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